NPN Silicon General Purpose Amplifiers and Switches

Metal can (TO-39)

V_{CBO} up to 120V.

I_C up to 750mA. P_{TOT} = 800mW @ 25°C.

Outline Drawing No. 66 applies.

REFERENCE TABLE

	Max. ratings			Characteristics @ 25°C						
	V_{CBO} (V)	V_{CEO} (V)	I_C (A)	h_{FE} @ I_C min.	h_{FE} @ I_C max.	(I_C mA)	I_{CBO} max. (nA)	at V_{CB} (V)	F_T Typ. MHz	Stock No.
BSY51	60	25	0.5	40	120	150	100	30	100	**27775E**
BSY52	60	25	0.5	100	300	150	100	30	130	**27776C**
BSY53	75	30	0.75	40	120	150	10	60	100	**27777A**
BSY54	75	30	0.75	100	300	150	10	60	145	**27778X**
BSY55	120	80	0.5	40	120	150	10	90	100	**27779H**
BSY56	120	80	0.5	100	300	150	10	90	145	**27780X**
BSY87	100	60	0.5	40	120	150	10	75	100	**27781R**
BSY88	100	60	0.5	100	300	150	10	75	145	**27782G**
BSY90	60	25	0.5	250	—	150	10	30	170	**27783E**
2N1613	75	50	0.5	30	100	1	10	60	80	**1046X**
2N1711	75	50	0.5	50	200	1	10	60	100	**1047R**
2N1893	120	80	0.5	30	100	1	10	90	75	**1045B**

NPN Silicon High Speed Switching Transistors

Metal can (TO-18).

Silicon planar epitaxial construction.

V_{EBO} = 5V. P_{TOT} = 300 mW @ 25°C.

Outline Drawing No. 65 applies.

REFERENCE TABLE

	Max. ratings			Characteristics @ 25°C							
	V_{CBO} (V)	V_{CEO} (V)	I_{CM} (mA)	h_{FE} @ I_C min.	mA	I_{CBO} @ V_{CB} max. (nA)	(V)	$V_{CE(sat)}$ @ I_C/I_B max. (V)	(mA)	f_T min. (MHz)	Stock No.
BSY95A	20	15	100	50	10	50	16	0.35	10/0.35	200	**1106H**
BSY27	20	15	100	40	10	25	9	0.35	10/1	200	**31273C**
2N706	25	—	50	20	10	500	15	0.6	10/1	200	**1130H**
2N706A	25	15	50	20	1	500	15	0.6	10/1	200	**1131F**
2N708	40	15	100	30	10	25	20	0.4	10/1	300	**1133B**
2N743	20	12	200	10	100	1000	20	1.0	100/10	300	**14093E**
2N744	20	12	200	20	100	1000	20	1.0	100/10	300	**27797D**
2N753	25	15	50	40	1	500	15	0.6	10/1	200	**27798B**
2N914	40	15	500	30	10	25	20	0.7	200/20	300	**1136G**
2N2368	40	15	500	20	10	400	20	0.25	10/1	500	**1128G**
2N2369	40	15	500	40	10	400	20	0.25	10/1	500	**7862E**
2N2369A	40	15	500	40	10	400	20	0.2	10/1	500	**1140D**